

Search Hist. (9 pp.) ~~10/27~~ (01/28/06)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:57
L3	6622	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:57
L4	2	3 and (sige silicon adj germanium).ti,ab,clm. and cmos near1 invert?r and (stack stacking stacked) near10 (pfet nfet pmos pmosfet pmisfet nmis nmisfet nmos nmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:59
L5	2	3 and (sige silicon adj germanium).ti,ab,clm. and cmos near1 invert?r and (stack stacking stacked) near10 (pfet nfet pmos pmosfet pmisfet nmis nmisfet nmos nmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 14:00
L6	2	("6882010").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 14:01
S1	4	"264914".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/20 09:44
S2	6	"760087".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S3	3	("6808971").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S4	1	"6429085".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:27
S5	1	"5006913".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:42
S6	1	"4768076".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:43

S7	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:44
S8	8	("4692994") or ("4768076") or ("5006913") or ("6429085")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 07:44
S9	1	(US-20040145399-\$.did.	US-PGPUB	OR	OFF	2005/09/07 07:45
S10	0	battacharyya.in. and strained and (sige gesi si-ge ge-si silicon adj germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S11	0	battacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S12	644	bhattacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57
S13	73	bhattacharyya.in. and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57
S14	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:57
S15	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:58
S16	35	bhattacharyya.in. and cmos and (thin adj film TFT) and strained. clm. and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:17

S17	11	(inverter inverter).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:24
S18	11	(inverter inverter CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S19	34	(inverter inverter CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S20	5	(inverter inverter CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and @ad<"20020311"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 10:33
S21	2	("5298452").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:46
S22	191	speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:47
S23	1	improve near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:49

S24	44	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 11:06
S25	49	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:09
S26	14	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter) and (single adj crystal monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:08
S27	23	"6251751"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:41
S28	18	S27 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S29	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S30	1	S29 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:19
S31	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22
S32	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22
S33	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:25

S34	28	polycrystalline near4 silicon adj germanium near10 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:26
S35	8	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S36	1	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls. and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S37	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
S38	2	silicon adj germanium near4 band adj gap near4 wide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
S39	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:12
S40	37	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:14
S41	10	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:20
S42	4900	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/07 16:20
S43	139	S42 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22

S44	16	S42 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge.sub."\$4"Si.sub."\$4) and (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22
S45	4	((("6251751") or ("5298452")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 21:18
S46	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 22:05
S47	1418	(pfet pmos pmosfet pmisfet) near6 (above below) near6 (nfet nmos nmosfet nmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 22:06
S48	1480	(pfet pmos pmosfet pmisfet) near6 (above below) near6 (nfet nmos nmosfet nmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:06
S49	363	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:07
S50	44	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and (silicon si) near3 (ge germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:07
S51	57	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:08
S52	25	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:09

S53	25	(pfet pmos pmosfet pmissfet) near3 (above below) near3 (nfet nmos nmosfet nmissfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:10
S54	5	(pfet pmos pmosfet pmissfet) near3 (above below) near3 (nfet nmos nmosfet nmissfet) and (cmos cmosfet) near4 invert?r and ((silicon si) near3 (ge germanium) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:12
S55	5	(pfet pmos pmosfet pmissfet) near3 (above below) near3 (nfet nmos nmosfet nmissfet) and (cmos cmosfet) near4 invert?r and (((silicon si) near3 (ge germanium)) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:19
S56	107	stack\$3 near4 (pfet pmos pmosfet pmissfet) near4 (nfet nmos nmosfet nmissfet) and (inverter inverter)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:43
S57	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:23
S58	1	"3793721".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S59	1	"4467518".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S60	1	"4489478".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S61	1	"4498226".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:25
S62	1	"4502202".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S63	1	"4555843".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S64	1	"4603468".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S65	1	"4649627".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S66	179	stack\$3 near4 (pfet pmos pmosfet pmissfet) near4 (nfet nmos nmosfet nmissfet)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:43
S67	1	(US-20040145399-\$.did.	US-PGPUB	OR	OFF	2006/01/29 08:25

S68	0	S67 and composition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 08:25
S69	1	S67 and semiconductor adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 08:25
S70	1	S67 and semiconductor adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 08:43
S71	252	graded near2 contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 08:43
S72	0	graded near2 contact and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S73	0	(grade grading graded) near2 (contact via) and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S74	5	(grade grading graded) near2 (contact via interconnect interconnection interconnexion) and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S75	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2006/01/29 10:51
S76	0	(US-20040145399-\$).did. and (composition composed grade graded grading)	US-PGPUB	OR	ON	2006/01/29 10:52
S77	1	(US-20040145399-\$).did. and (composition composed grade graded grading doping concentration)	US-PGPUB	OR	ON	2006/01/29 11:31
S78	4	cmos adj inverter near6 computer. ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:32
S79	4	cmos adj inverter near20 computer. ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:32
S80	22	cmos adj inverter. ti,ab,clm. and computer. ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:33

S81	0	cmos adj inverter near10 (logic adj circuit).ti,ab,clm. and computer near10 (logic adj circuit).ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:34
S82	0	cmos adj inverter near20 (logic adj circuit).ti,ab,clm. and computer near20 (logic adj circuit).ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:35
S83	10	cmos adj inverter near3 computer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 11:37
S84	7	cmos adj inverter near6 computer not bhattacharyya.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 11:42
S85	2	("5774008").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 12:10
S86	13	strained near10 relaxed near10 lattice and CMOS near1 invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 13:27